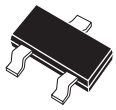
查询CMPD2005S供应商

CMPD2005S

SURFACE MOUNT
DUAL, IN SERIES
HIGH VOLTAGE
SILICON SWITCHING DIODES



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CMPD2005S contains two (2) High Voltage Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SOT-23 surface mount package, designed for applications requiring high voltage capability.

MARKING CODE: DB5

MAXIMUM RATINGS (T_A=25℃)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	300	V
Peak Repetitive Reverse Voltage	V_{RRM}	350	V
Peak Repetitive Reverse Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current, tp= 1μs	I_{FSM}	4.0	A
Forward Surge Current, tp= 1s	I_{FSM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	V_R=280V			100	nA
I_R	V_R=280V, T_A=150°C			100	μA
BV_R	I_R=100μA	350			V
V_F	I_F=20mA			0.87	V
V_F	I_F=100mA			1.0	V
V_F	I_F=200mA			1.25	V
C_T	V_R=0, f=1.0 MHz			5.0	pF
t_{rr}	I_R=I_F=30mA, Rec. to 3.0mA, R_L=100Ω			50	ns

R1 (6-August 2003)

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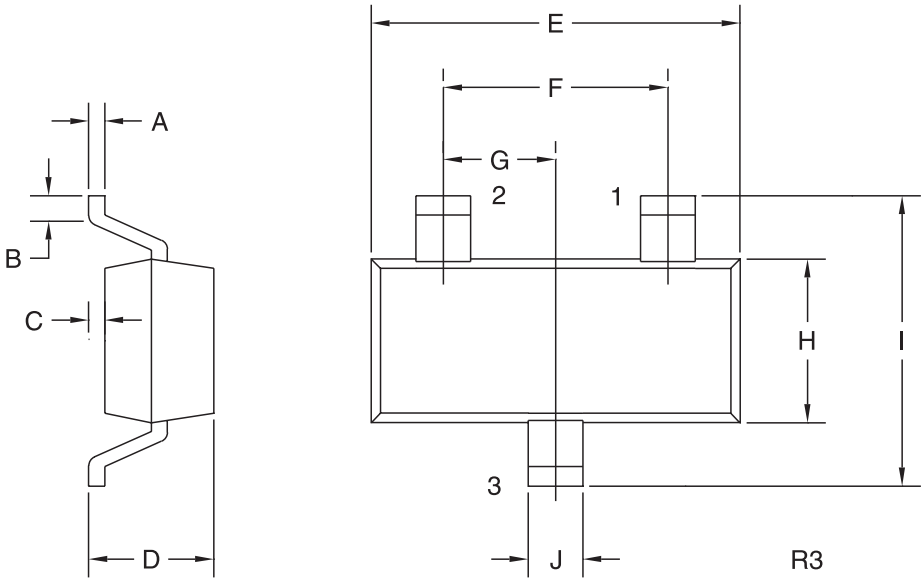
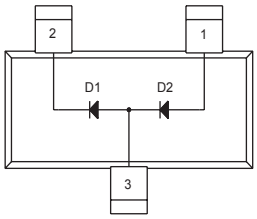
HIGH VOLTAGE
SILICON SWITCHING DIODES

SOT-23 CASE - MECHANICAL OUTLINE



MARKING CODE: DB5



LEAD CODE:
1) **Anode D2**
2) **Cathode D1**
3) **Anode D1, Cathode D2**

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (6-August 2003)